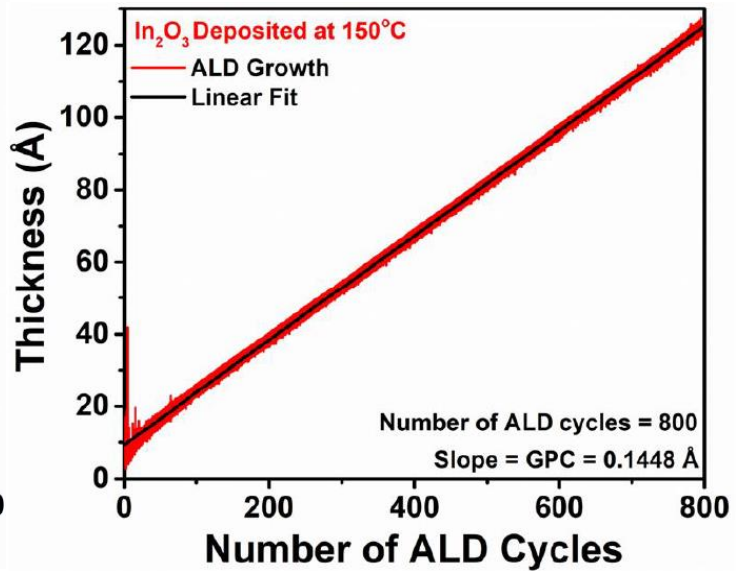
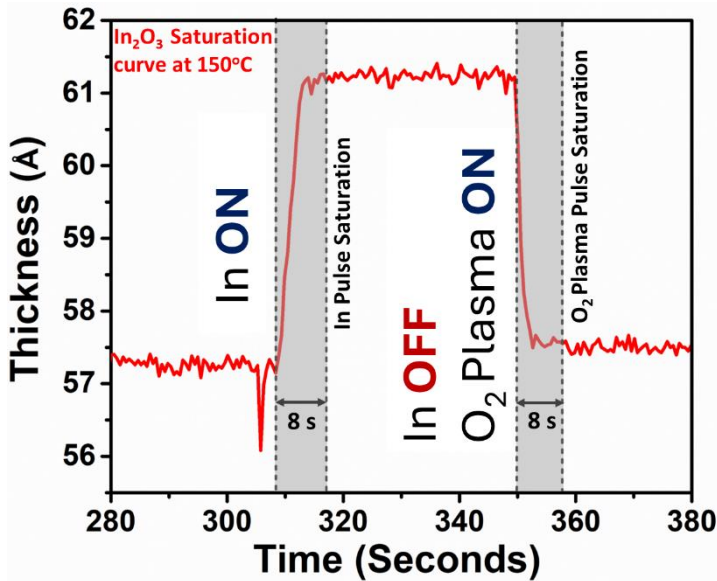


Plasma Enhanced Atomic Layer Deposition of Hydrogen Free In_2O_3 Thin Films with High Charge Carrier Mobility

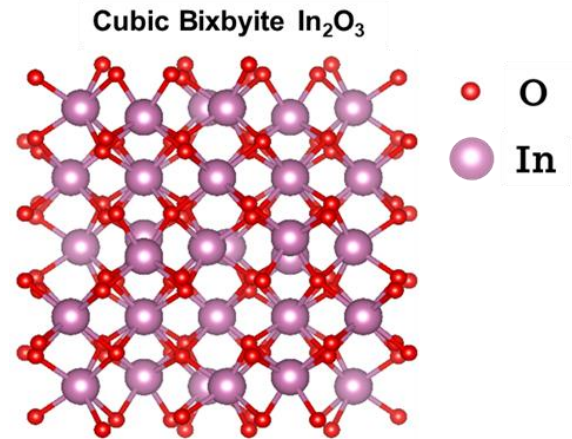
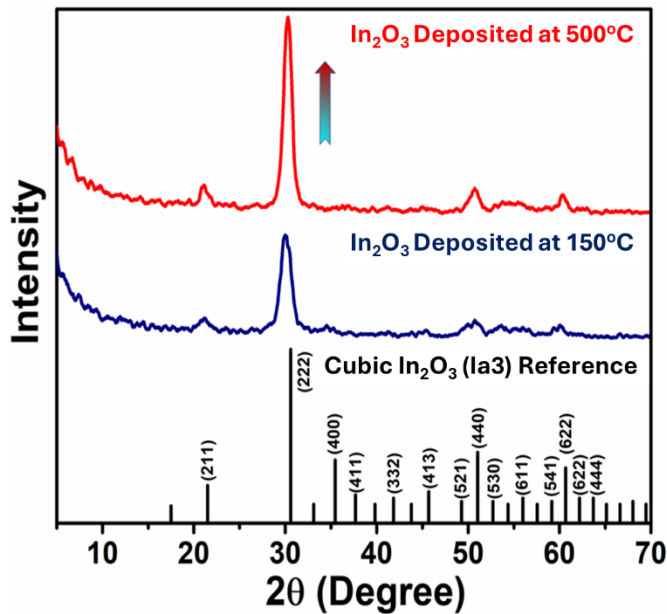
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Figures:

1. In-situ Ellipsometry Saturation Curves at 150°C:



2. Grazing Incidence X-ray Diffraction (GIXRD) Pattern and Crystal Structure:



References for Abstract:

1. Si, M.; Hu, Y.; Lin, Z.; Sun, X.; Charnas, A.; Zheng, D.; Lyu, X.; Wang, H.; Cho, K.; Ye, P. D. Why In₂O₃ Can Make 0.7 Nm Atomic Layer Thin Transistors. *Nano Lett.* **2021**, *21* (1), 500–506.
2. Lin, Z.; Si, M.; Askarpour, V.; Niu, C.; Charnas, A.; Shang, Z.; Zhang, Y.; Hu, Y.; Zhang, Z.; Liao, P.-Y.; Cho, K.; Wang, H.; Lundstrom, M.; Maassen, J.; Ye, P. D. Nanometer-Thick Oxide Semiconductor Transistor with Ultra-High Drain Current. *ACS Nano* **2022**, *16* (12), 21536–21545.